

NPN Epitaxial Silicon Transistor

KSC2073

TO-220-3LD CASE 340AT

Features

- TV Vertical Deflection Output
- Complement to KSA940
- Collector-Base Voltage : V_{CBO} = 150 V
- These Devices are Pb-Free and Halide Free

ABSOLUTE MAXIMUM RATINGS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted.})$

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	150	V
V _{CEO}	VCEO Collector-Emitter Voltage VEBO Emitter-Base Voltage IC Collector Current PC Collector Dissipation (T _C =25°C)		V
V _{EBO}			V
I _C			Α
P _C			W
T _J	T _J Junction Temperature		°C
T _{STG}	T _{STG} Storage Temperature		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

MARKING DIAGRAMS



- 1: Base
- 2: Collector 3: Emitter



AYWWZZ C2073-2

- 1: Base 2: Collector
- 3: Emitter

= Assembly Plant Code YWW = 3-Digit Date Code

2

(Year and Week) = 2-Digit Lot Code ZΖ C2073, C2073-2 = Specific Device Code

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 2 of this data sheet.

KSC2073

ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise noted.})$

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 500 \mu A, I_E = 0$	150	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA, I _B = 0	150	-	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 500 μA, I _C = 0	5	-	-	V
I _{CBO}	Collector Cut-Off Current	V _{CB} = 120 V, I _E = 0	-	-	10	μΑ
h _{FE}	DC Current Gain	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}$	40	75	140	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$	-	-	1	V
f _T	Current Gain Bandwidth Product	V _{CE} = 10 V, I _C = 0.5 A	-	4	-	MHz
C _{ob}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	50	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

h_{FE} CLASSIFICATION

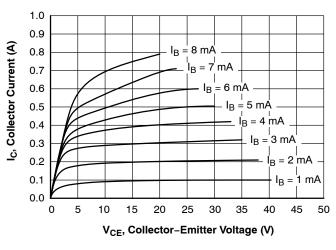
Classification	H1	H2		
h _{FE}	40 ~ 80	60 ~ 125		

ORDERING INFORMATION

Device	Package	Marking	Shipping
KSC2073TU	TO-220-3LD (Pb-Free)	C2073	1000 Units / Tube
KSC2073H2TU	1	C2073-2	

KSC2073

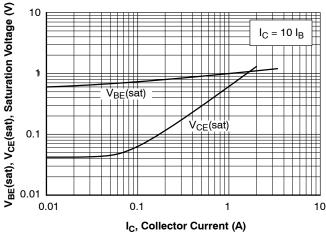
TYPICAL PERFORMANCE CHARACTERISTICS



1000 V_{CE} = 10 V V_{CE} = 10 V

Figure 1. Static Characteristic

Figure 2. DC Current Gain



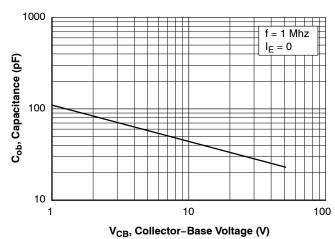
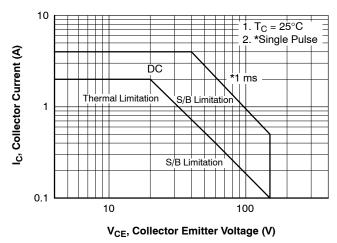


Figure 3. Base–Emitter Saturation Voltage Collector–Emitter Saturation Voltage

Figure 4. Collector-Emitter On Voltage



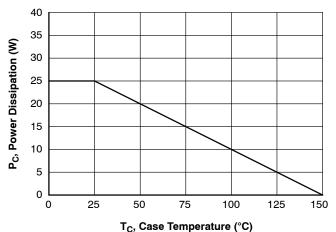
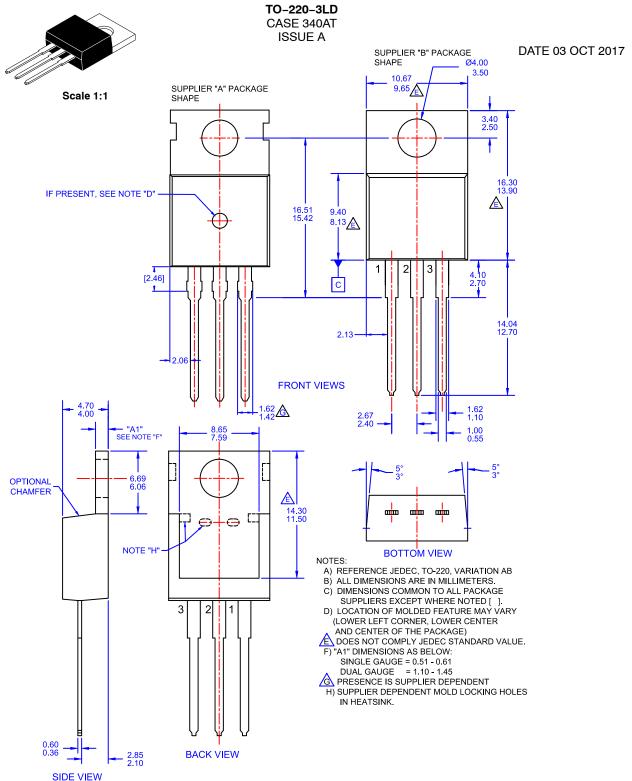


Figure 5. Safe Operating Area

Figure 6. Power Derating



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